

isc N-Channel Mosfet Transistor

FRM230

• FEATURES

- 8A, 200V, $R_{DS(on)} = 0.5\Omega$
- Second Generation Rad Hard MOSFET Results From New Design Concepts
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

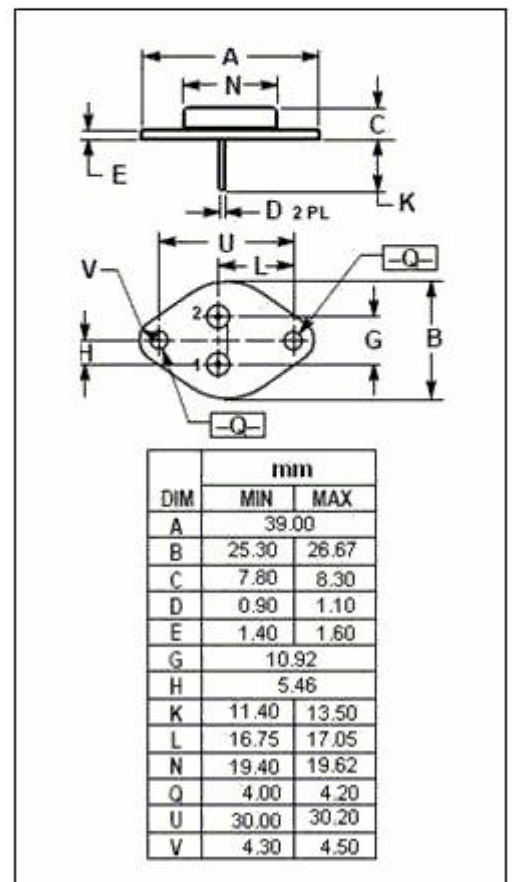
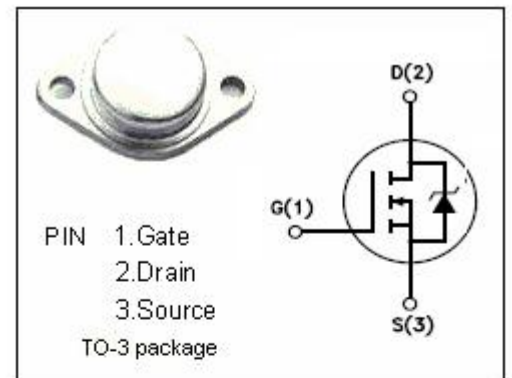
It is specially designed and processed to exhibit minimal characteristic changes to total dose and neutron exposures. Design and processing efforts are also directed to enhance survival to heavy ion (SEE) and/or dose rate(GAMMA DOT) exposure

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage ($V_{GS}=0$)	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^\circ\text{C}$	8	A
	Drain Current-continuous@ $TC=100^\circ\text{C}$	5	A
I_{DM}	Drain Current-Single Pulsed	24	A
P_{tot}	Total Dissipation@ $TC=25^\circ\text{C}$	75	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.67	$^\circ\text{C/W}$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	60	$^\circ\text{C/W}$



isc N-Channel Mosfet Transistor

FRM230

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	200			V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	2.0		4.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}; I_D=5\text{A}$			0.5	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=200\text{V}; V_{GS}=0$			25	μA
V_{SD}	Diode Forward Voltage	$I_S=8\text{A}; V_{GS}=0$			1.8	V
$t_{d(on)}$	Turn-on Delay Time	$I_D=8\text{A};$ $V_{DD}=100\text{V};$ $R_{GS}=25\ \Omega$			30	ns
t_r	Rise Time				130	
$t_{d(off)}$	Turn-off Delay Time				150	
t_f	Fall Time				80	

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.